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Correction: HfO_2-based ferroelectric synaptic devices: challenges and engineering solutions

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Correction for 'HfO_2-based ferroelectric synaptic devices: challenges and engineering solutions' by Taegyu Kwon *et al.*, *Chem. Commun.*, 2025, **61**, 3061–3080, **https://doi.org/10.1039/d4cc05293e**.

The authors regret that a sentence was omitted from the Acknowledgements in the original article. The additional sentence should read ''The aforementioned NRF project RS-2024-00441473 is based on the official partnership with the CHIP JU project ViTFOX GA No 101194368.''

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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